

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Takayoshi Sawayama.

Serial No.: 09/754,277

RECEIVED

Group Art Unit: 1763

Examiner: L. Alejandro

Mulero

Filed: January 5, 2001

For: PLASMA ETCHING APPARATUS

48B 2125103 mw

Honorable Commissioner of Patents

Washington, D.C. 20231

Date: February 10, 2003

## **Preliminary Amendment**

Sir:

A Request for Continued Prosecution (RCE) being enclosed herewith, it is respectfully requested that the following amendments and remarks be considered upon initial examination of the above application.

## In the Specification

(1.) At page 2, line 4, please replace the paragraph that begins "When the gasintroducing plate 4..." with the following paragraph:

When the gas-introducing plate 4 lying within the processing chamber of the etching apparatus is used up, the gas-introducing plate 4 becomes thin as shown in Fig. 2. Further, the gas holes 3 defined in the gas-introducing plate 4 reach a given size or more respectively, the following would occur. Plasma enters the backside (cooling plate side) of the gas-introducing plate from the etching-processing chamber 9 through the enlarged